



# FQH18N50V2 Information



For Reference Only

Part Number FQH18N50V2

ManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor Products<br/>Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 500V 20A TO-247

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# FQH18N50V2 Specifications

Manufacturer Part Number         FQH18N50V2           Manufacturer         Fairchild/ON Semiconductor           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-247-3           Series         QFET?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         500V           Current - Continuous Drain (Id) @ 25°C         20A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         350C @ 10V           Input Capacitance (Ciss) (Max) @ Vds         3290pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         277W (Tc)           Rds On (Max) @ Id, Vgs         265 mOhm @ 10A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-247           Package / Case         TO-247-3		
Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-247-3           Series         QFET?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         500V           Current - Continuous Drain (Id) @ 25°C         20A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         55nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         3290pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         277W (Tc)           Rds On (Max) @ Id, Vgs         265 mOhm @ 10A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-247	Manufacturer Part Number	FQH18N50V2
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C20A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs55nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3290pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)277W (Tc)Rds On (Max) @ Id, Vgs265 mOhm @ 10A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247	Package	TO-247-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C20A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs55nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3290pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)277W (Tc)Rds On (Max) @ Id, Vgs265 mOhm @ 10A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247	Series	QFET?
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Drive Voltage (Max Rds On, Min Rds On) $Vgs(th)$ (Max) @ Id $SV$ @ $250\mu A$ Gate Charge (Qg) (Max) @ Vgs $SSIDE SIDE SIDE SIDE SIDE SIDE SIDE SIDE$	Drain to Source Voltage (Vdss)	500V
Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Supplier Device Package  5V @ 250μA  55nC @ 10V  3290pF @ 25V  230V  277W (Tc)  277W (Tc)  265 mOhm @ 10A, 10V  -55°C ~ 150°C (TJ)  Through Hole	Current - Continuous Drain (Id) @ 25°C	20A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Through Hole  Supplier Device Package  55nC @ 10V  3290pF @ 25V  ±30V	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Coperating Type  Through Hole  Supplier Device Package  3290pF @ 25V  230V  277W (Tc)  277W (Tc)  277W (Tc)  265 mOhm @ 10A, 10V  -55°C ~ 150°C (TJ)  Through Hole	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)277W (Tc)Rds On (Max) @ Id, Vgs265 mOhm @ 10A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247	Gate Charge (Qg) (Max) @ Vgs	55nC @ 10V
FET Feature -  Power Dissipation (Max) 277W (Tc)  Rds On (Max) @ Id, Vgs 265 mOhm @ 10A, 10V  Operating Temperature -55°C ~ 150°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-247	Input Capacitance (Ciss) (Max) @ Vds	3290pF @ 25V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  265 mOhm @ 10A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-247	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs265 mOhm @ 10A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-247	Power Dissipation (Max)	277W (Tc)
Mounting Type Through Hole Supplier Device Package TO-247	Rds On (Max) @ Id, Vgs	265 mOhm @ 10A, 10V
Supplier Device Package TO-247	Operating Temperature	-55°C ~ 150°C (TJ)
	Mounting Type	Through Hole
Package / Case TO-247-3	Supplier Device Package	TO-247
	Package / Case	TO-247-3
Report errors?		Report errors?

## FQH18N50V2 Guarantees



### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## FQH18N50V2 Payment Methods





















### FQH18N50V2 Shipping Methods













If you have any question about FQH18N50V2, please do not hesitate to contact us!

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